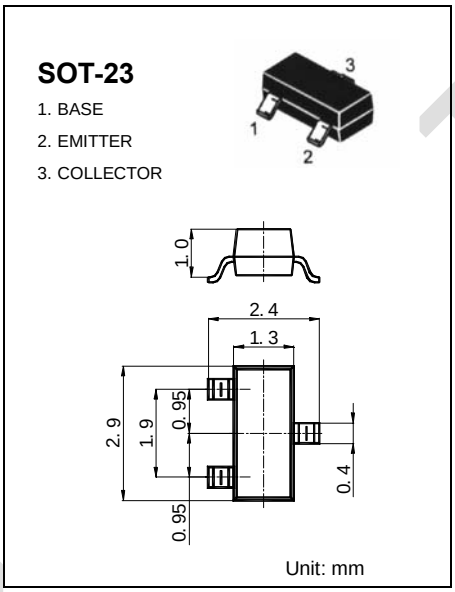
SOT-23 Plastic-Encapsulate Transistors

BCW60C TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.25 W (Tamb=25℃)

Collector current

I_{CM}: 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 32 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 10μA, I_E=0	32		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 1mA, I_B=0	32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=32V, I_E=0		0.02	μA
Collector cut-off current	I_{EBO}	V_{EB}=4V, I_C=0		0.02	μA
DC current gain	h_{FE1}	V_{CE}=5V, I_C= 10μA	40		
	h_{FE2}	V_{CE}=5V, I_C= 2mA	250	460	
	h_{FE3}	V_{CE}=5V, I_C= 50mA	100		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=0.25mA		0.35	V
		I_C=50mA, I_B=1.25mA		0.55	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10mA, I_B=0.25mA		0.85	V
		I_C=50mA, I_B=1.25mA		1.05	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C= 2mA	0.55	0.75	V
Transition frequency	f_T	V_{CE}= 5V, I_C=10mA, f=100MHz	100		MHz
Output capacitance	C_{ob}	V_{CB}= 10V, I_E=0, f=1MHz		5	pF

Marking	**AC**